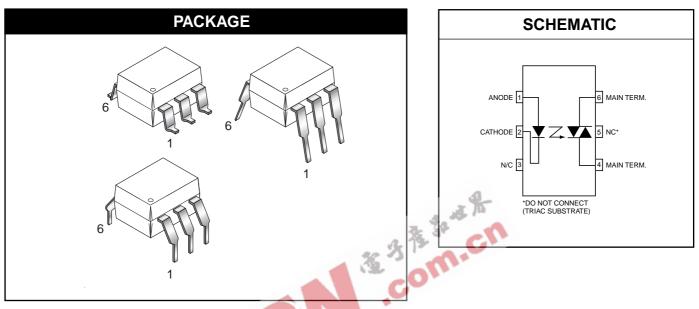


MOC3010M MOC3011M MOC3012M **MOC3020M** MOC3021M MOC3022M MOC3023M



### DESCRIPTION

The MOC301XM and MOC302XM series are optically isolated triac driver devices. These devices contain a GaAs infrared emitting diode and a light activated silicon bilateral switch, which functions like a triac. They are designed for interfacing between electronic controls and power triacs to control resistive and inductive loads for 115 VAC operations.

### **FEATURES**

- ٠ Excellent I<sub>FT</sub> stability—IR emitting diode has low degradation
- High isolation voltage-minimum 5300 VAC RMS •
- Underwriters Laboratory (UL) recognized—File #E90700
- Peak blocking voltage
  - 250V-MOC301XM
  - 400V-MOC302XM
- VDE recognized (File #94766)
  - Ordering option V (e.g. MOC3023VM)

### **APPLICATIONS**

- Industrial controls •
- Traffic lights •

•

- Solenoid/valve controls
- - Vending machines ٠
- Solid state relay
- Lamp ballasts •
- Static AC power switch •
- Incandescent lamp dimmers
- Motor control ٠



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ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
Parameters	Symbol	Device	Value	Units	
TOTAL DEVICE					
Storage Temperature	T <sub>STG</sub>	All	-40 to +150	°C	
Operating Temperature	T <sub>OPR</sub>	All	-40 to +85	°C	
Lead Solder Temperature	T <sub>SOL</sub>	All	260 for 10 sec	°C	
Junction Temperature Range	ТJ	All	-40 to +100	°C	
Isolation Surge Voltage <sup>(1)</sup> (peak AC voltage, 60Hz, 1 sec duration)	V <sub>ISO</sub>	All	7500	Vac(pk)	
Total Device Power Dissipation @ 25°C			330	mW	
Derate above 25°C		P <sub>D</sub> All		mW/°C	
EMITTER	32				
Continuous Forward Current	I <sub>F</sub>	All	60	mA	
Reverse Voltage	V <sub>R</sub>	All	3	V	
Total Power Dissipation 25°C Ambient	PD	All	100	mW	
Derate above 25°C	ГD		1.33	mW/°C	
DETECTOR					
Off-State Output Terminal Voltage	V <sub>DRM</sub>	MOC3010M/1M/2M MOC3020M/1M/2M/3M	250 400	V	
Peak Repetitive Surge Current (PW = 1 ms, 120 pps)	I <sub>TSM</sub>	All	1	А	
Total Power Dissipation @ 25°C Ambient	Pp All -		300	mW	
Derate above 25°C	P <sub>D</sub>	All	4	mW/°C	

#### Note

1. Isolation surge voltage, V<sub>ISO</sub>, is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.



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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25°C Unless otherwise specified)							
INDIVIDUAL COMPONENT CHARACTERISTICS							
Parameters	Test Conditions	Symbol	Device	Min	Тур	Max	Units
EMITTER							
Input Forward Voltage	I <sub>F</sub> = 10 mA	V <sub>F</sub>	All		1.15	1.5	V
Reverse Leakage Current	V <sub>R</sub> = 3 V, T <sub>A</sub> = 25°C	I <sub>R</sub>	All		0.01	100	μA
DETECTOR							
Peak Blocking Current, Either Direction	Rated V <sub>DRM</sub> , I <sub>F</sub> = 0 (note 1)	I <sub>DRM</sub>	All		10	100	nA
Peak On-State Voltage, Either Direction	$I_{TM}$ = 100 mA peak, $I_F$ = 0	V <sub>TM</sub>	All		1.8	3	V

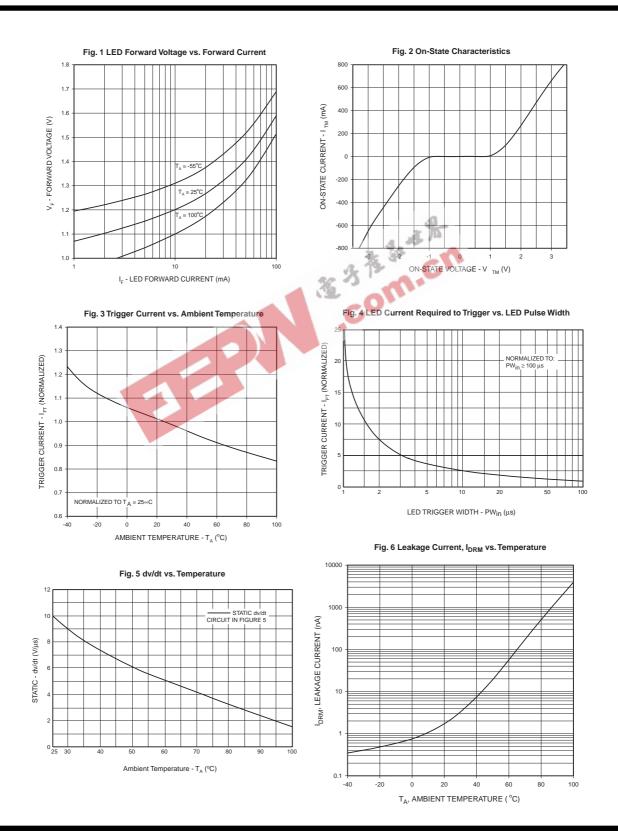
		2	为意望	cn			
<b>TRANSFER CHARACTERISTICS</b> (T <sub>A</sub> = 25°C Unless otherwise specified.)							
DC Characteristics	Test Conditions	Symbol	Device	Min	Тур	Max	Units
LED Trigger Current		IFT	MOC3020M			30 15 10 5	mA
			MOC3010M				
			MOC3021M				
	Voltage = 3V (note 3)		MOC3011M				
			MOC3022M				
			MOC3012M				
			MOC3023M				
Holding Current, Either Direc	ction	Ι <sub>Η</sub>	All		100		μA

#### Note

- 1. Test voltage must be applied within dv/dt rating.
- 2. This is static dv/dt. See Figure 5 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- All devices are guaranteed to trigger at an I<sub>F</sub> value less than or equal to max I<sub>FT</sub>. Therefore, recommended operating I<sub>F</sub> lies between max I<sub>FT</sub> (30 mA for MOC3020M, 15 mA for MOC3010M and MOC3021M, 10 mA for MOC3011M and MOC3022M, 5 mA for MOC3012M and MOC3023M) and absolute max I<sub>F</sub> (60 mA).



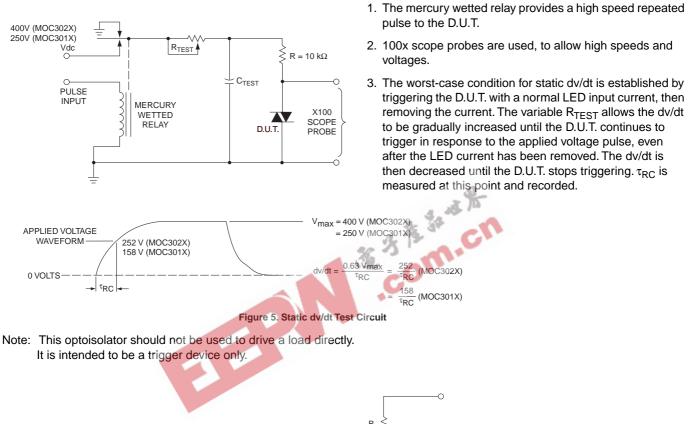
MOC3010M MOC3011M MOC3012M MOC3020M MOC3021M MOC3022M MOC3023M





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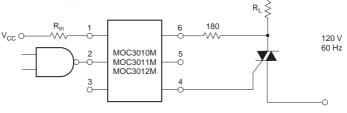


Figure 6. Resistive Load

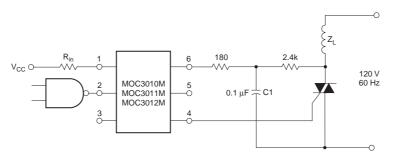
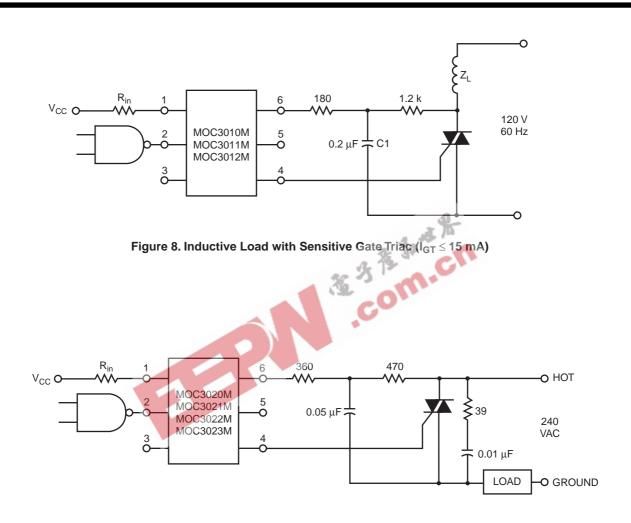


Figure 7. Inductive Load with Sensitive Gate Triac (I\_{GT}  $\leq$  15 mA)



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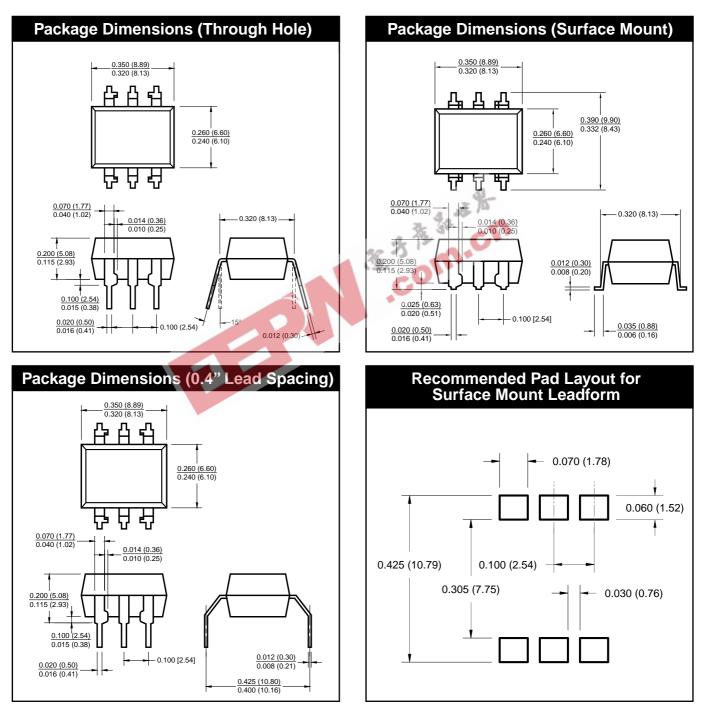
In this circuit the "hot" side of the line is switched and the load connected to the cold or ground side.

The 39 ohm resistor and  $0.01\mu$ F capacitor are for snubbing of the triac, and the 470 ohm resistor and 0.05  $\mu$ F capacitor are for snubbing the coupler. These components may or may not be necessary depending upon the particular and load used.

**Figure 9. Typical Application Circuit** 



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#### NOTE

All dimensions are in inches (millimeters)

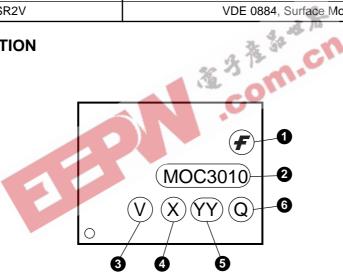


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#### **ORDERING INFORMATION**

Option	Order Entry Identifier	Description
S	S	Surface Mount Lead Bend
SR2	SR2	Surface Mount; Tape and reel
Т	Т	0.4" Lead Spacing
V	V	VDE 0884
ΤV	TV	VDE 0884, 0.4" Lead Spacing
SV	SV	VDE 0884, Surface Mount
SR2V	SR2V	VDE 0884, Surface Mount, Tape & Reel

#### MARKING INFORMATION

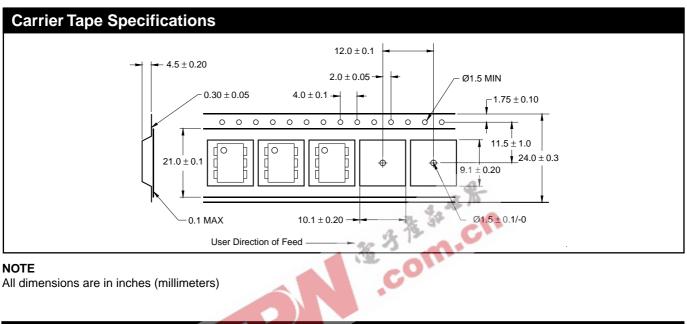


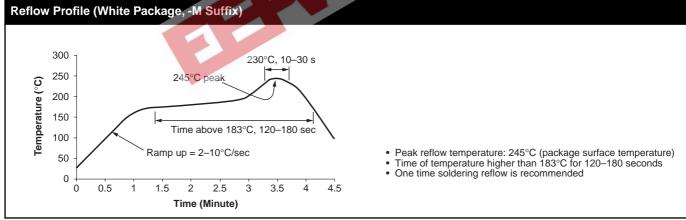
Definitions			
1	Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	One digit year code, e.g., '3'		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		
*Note – Par	ts that do not have the 'V' option (see definition 3 above) that are marked with		

\*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.



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  A critical component in device or system whereasonably expected to device or system, or to a significant injury of the user.
- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

